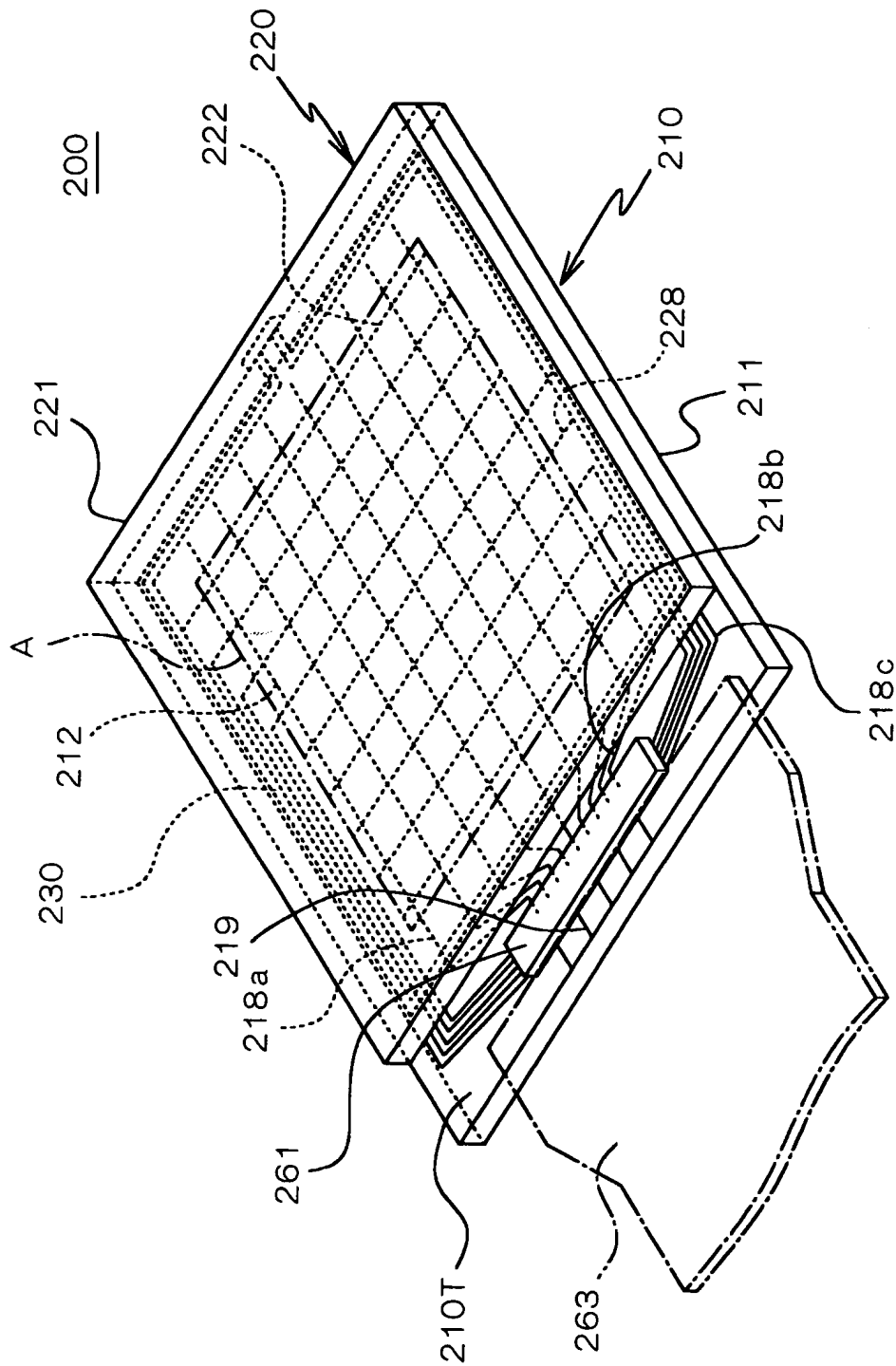
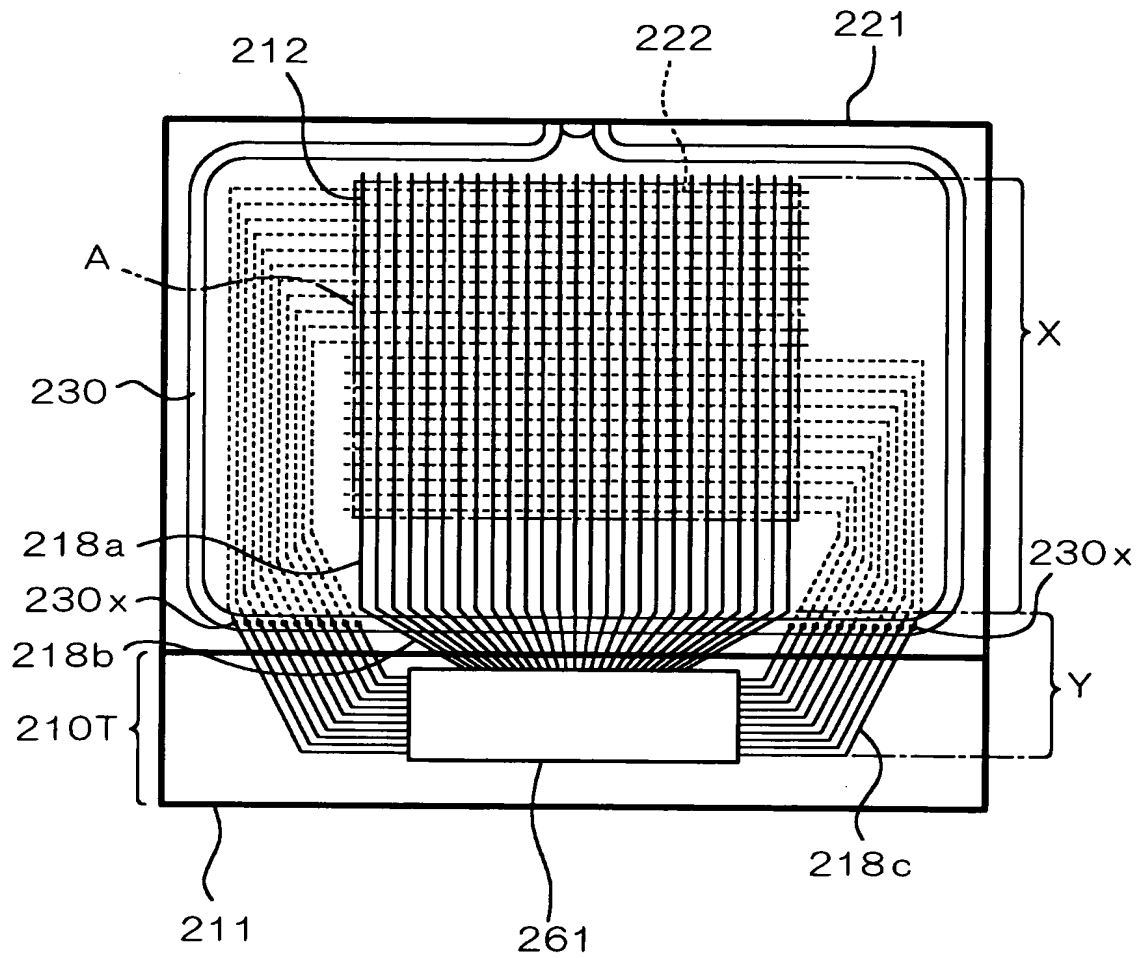


FIG. 1



A cross-sectional view of a semiconductor device 200. The device consists of a substrate 210 with a top surface 211 and a bottom surface 212. A layer 212Y is formed on the top surface 211. A layer 212X is formed on the bottom surface 212. A layer 211s is formed on the top surface 211. A layer 216 is formed on the top surface 211. A layer 215 is formed on the bottom surface 212. A layer 226 is formed on the top surface 211. A layer 223 is formed on the top surface 211. A layer 224 is formed on the top surface 211. A layer 222 is formed on the top surface 211. A layer 223BM is formed on the top surface 211. A layer 251 is formed on the top surface 211. A layer 250 is formed on the top surface 211. A layer 200P is formed on the top surface 211. A layer 232 is formed on the top surface 211. A layer 230 is formed on the top surface 211. A layer 240 is formed on the bottom surface 212. A layer 241 is formed on the bottom surface 212.

FIG. 3



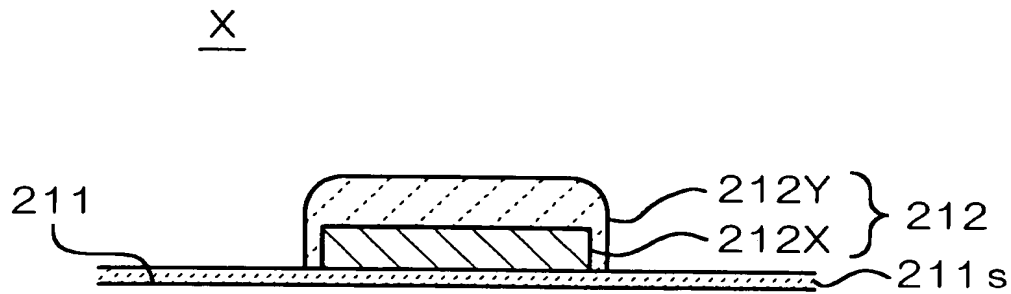


FIG. 4A

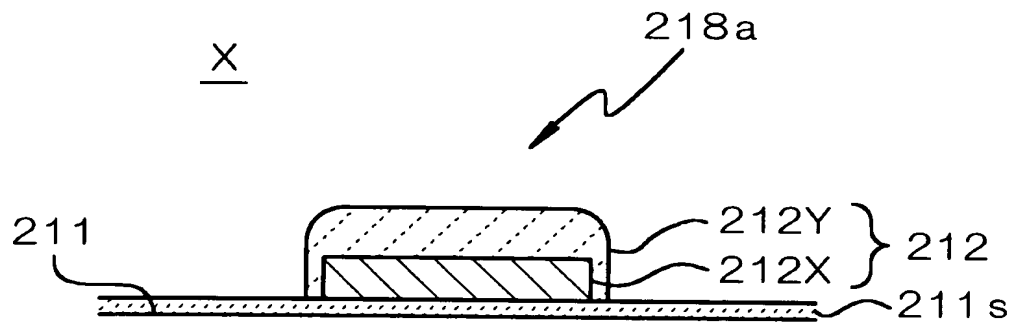


FIG. 4B

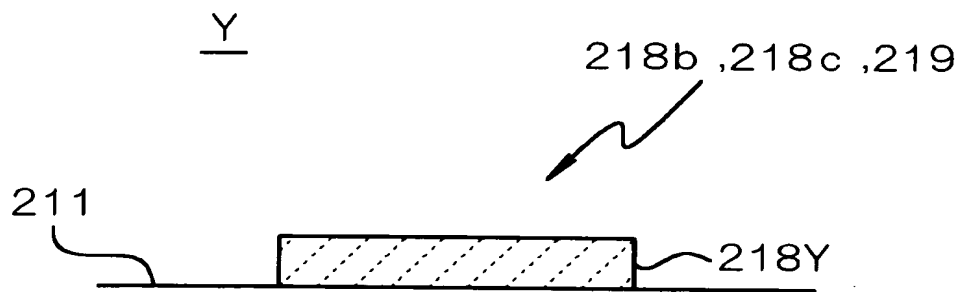


FIG. 4C

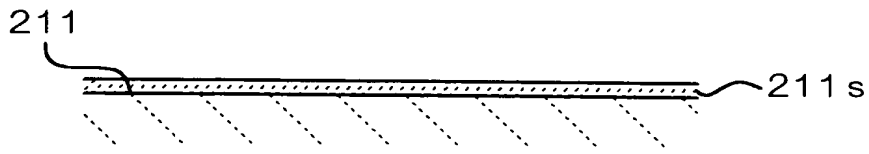


FIG. 5A

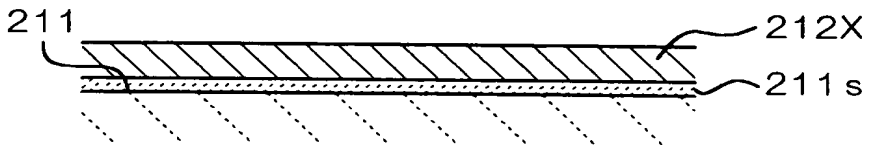


FIG. 5B

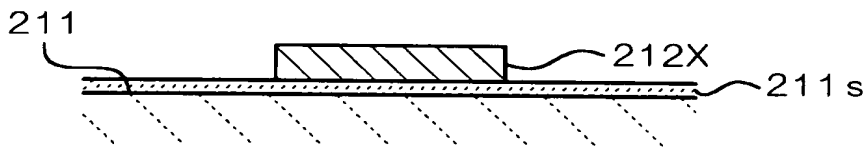


FIG. 5C

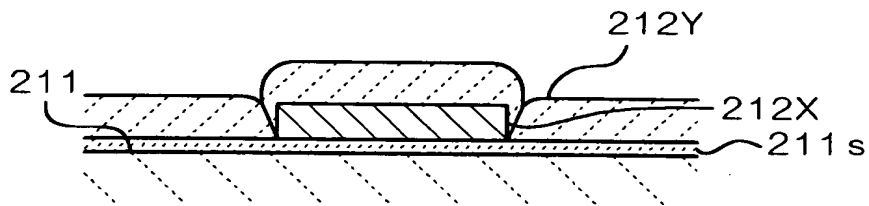


FIG. 5D

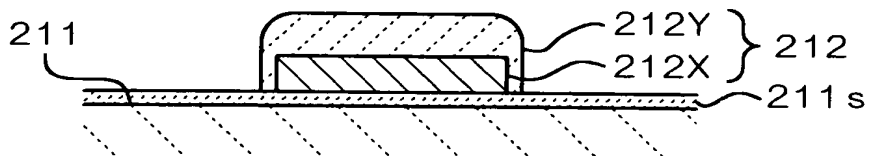


FIG. 5E

FIG. 6

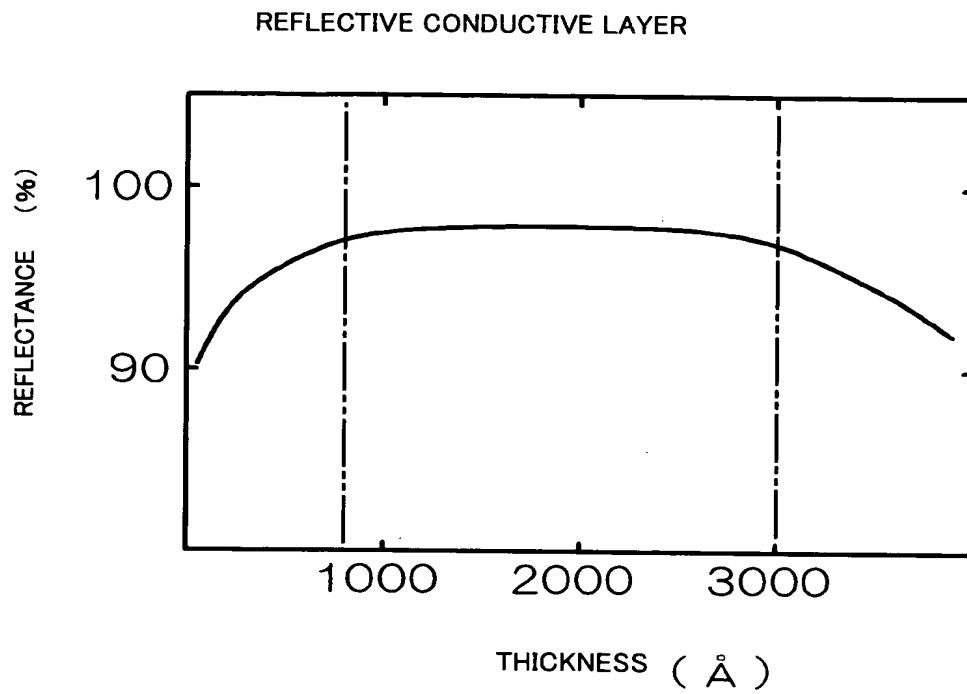


FIG. 7

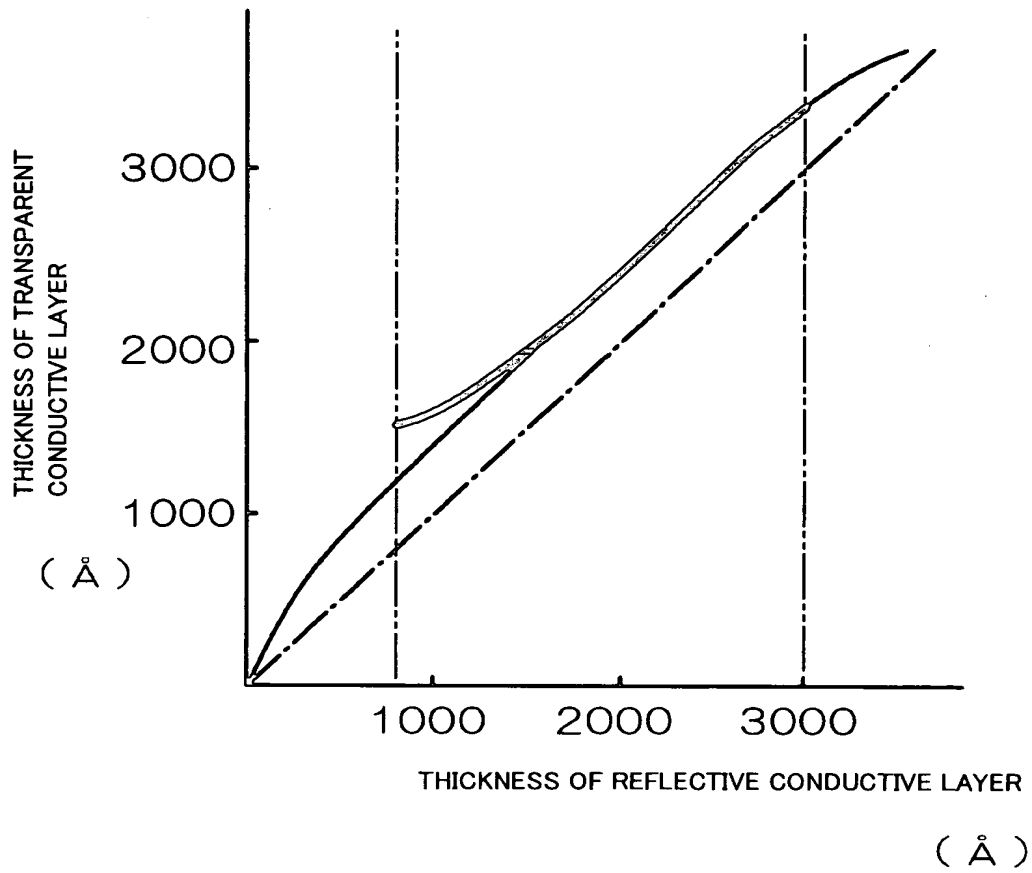


FIG. 8

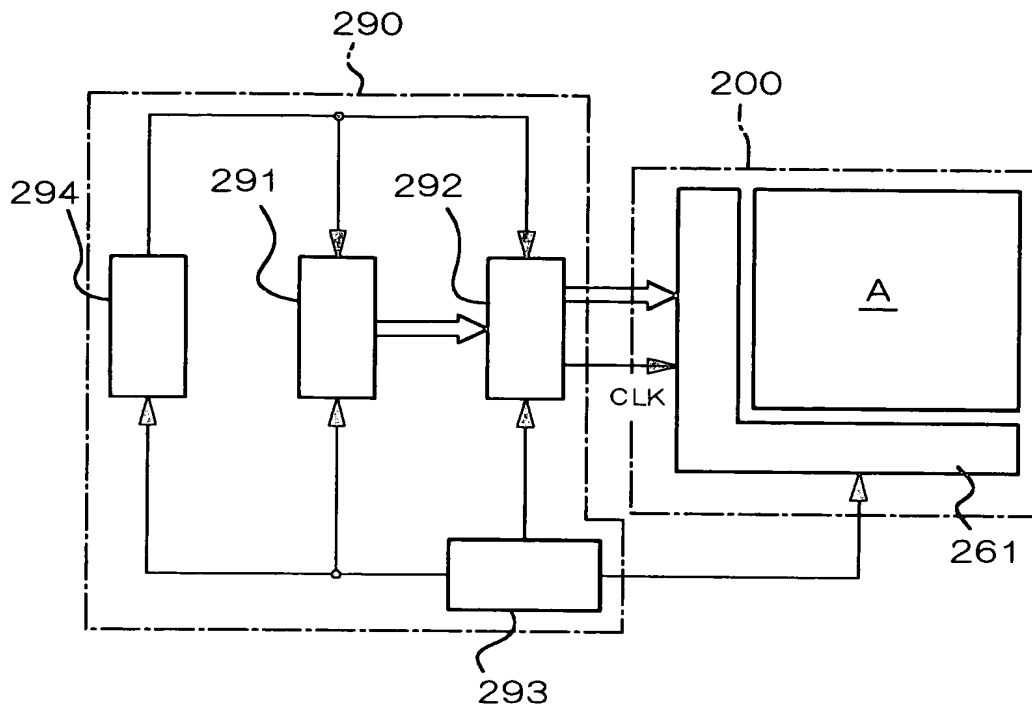


FIG. 9

